

32Mb Burst CellularRAM™ 1.0 Memory Addendum

MT45W2MW16BGB-708 AT

Features

- Single device supports asynchronous, page, and burst operations
- VCC, VCCQ Voltages
- 1.7V–1.95V VCC
- 1.7V–3.6V VCCQ
- Random Access Time: 70ns
- Burst Mode READ and WRITE Access
- 4, 8, 16 words, or continuous burst
- Burst wrap or sequential
- MAX clock rate: 80 MHz (^tCLK = 12.5ns)
- Burst initial latency: 50ns (4 clocks) @ 80MHz
- ^tACLK: 9ns @ 80MHz
- Page Mode Read Access
- Sixteen-word page size
- Interpage read access: 70ns
- Intrapage read access: 20ns
- Low Power Consumption
- Asynchronous READ: < 30mA
- Intrapage Read: < 15mA
- Initial access, burst READ:
(50ns [4 clocks] @ 80 MHz) < 30mA
- Continuous burst READ: < 18mA
- Standby: < 65µA (TYP at 25°C)
- Deep power-down: < 3µA (TYP)
- Low-Power Features
- On-chip Temperature Compensated Refresh (TCR)
- Partial Array Refresh (PAR)
- Deep Power-Down (DPD) Mode

Options

- Configuration:
2 Meg x 16
VCC Core Voltage Supply: 1.8V
VCCQ I/O Voltage Supply: 3.6V
- Package
54-ball VFBGA—”green”
- Timing
70ns access
80MHz
- Standby Power
Standard:
- Operating Temperature Range
Automotive (-40°C to +105°C)

Designator
MT45W2MW16B

GB

-70

8

None

AT

Part Number Example:
MT45W2MW16BGB-708AT

Parameter Relaxation

To support the automotive temperature range, -40°C to $+105^{\circ}\text{C}$, no change to the device specification is needed.



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This data sheet contains minimum and maximum limits specified over the complete power supply and temperature range for production devices. Although considered final, these specifications are subject to change, as further product development and data characterization sometimes occur.



Revision History

- Original document, Rev. A 04/07